

**METHOD OF MANUFACTURING TRENCH FIELD EFFECT
TRANSISTORS WITH TRENCHED HEAVY BODY**

09/405210

ABSTRACT OF THE DISCLOSURE

A process for manufacturing trench field effect transistors improves transistor ruggedness without compromising transistor cell pitch. Instead of a high dose implant and heat cycle, the process of the invention forms the transistor heavy
5 body by etching a trench into the body region and filling the heavy body trench with high conductivity material such as metal that makes contact to both the body and the source region.

SF 1011800 v2

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